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November 2013

## FQP3N30

# N-Channel QFET<sup>®</sup> MOSFET 300 V, 3.2 A, 2.2 $\Omega$

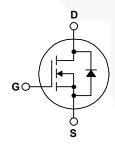
#### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### **Features**

- 3.2 A, 300 V,  $R_{DS(on)}$  = 2.2  $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 1.6 A
- Low Gate Charge (Typ. 5.5 nC)
- · Low Crss (Typ. 6 pF)
- · 100% Avalanche Tested





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FQP3N30	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		300	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°	C)	3.2	Α
	- Continuous (T <sub>C</sub> = 100	)°C)	2.02	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	12.8	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	140	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	3.2	A
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	5.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
$P_D$	Power Dissipation (T <sub>C</sub> = 25°C)		55	W
	- Derate above 25°C		0.44	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

### **Thermal Characteristics**

Symbol	Parameter	FQP3N30	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.27	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max. 62.5		°C/W

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP3N30	FQP3N30	TO-220	Tube	N/A	N/A	50 units

FI	actrica	I Chara	acteristics	
	ecuica	i Gilala	acteristics	T∩=

= 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	300			V
$\Delta BV_{DSS}$ / $\Delta T_J$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	;	0.35		V/°C
I <sub>DSS</sub>	Zara Oata Vallana Busin Ourset	V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 240 V, T <sub>C</sub> = 125°C			10	μА
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.6 A		1.65	2.2	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 1.6 A		1.75		S
C <sub>iss</sub> C <sub>oss</sub>	Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		40 6	50 8	pF pF
C <sub>rss</sub>	Reverse Transfer Capacitance			6	8	pF
Switch	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time $V_{DD} = 150 \text{ V}, I_D = 3.2 \text{ A},$			10	30	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		40	90	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			10	30	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4		25	60	ns
$Q_g$	Total Gate Charge	$V_{DS} = 240 \text{ V}, I_D = 3.2 \text{ A},$		5.5	7.0	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		1.5		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		2.5		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				3.2	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F	Forward Current			12.8	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 3.2 A			1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 3.2 A,		120		ns
	D D	dl / dt = 100 A/v.a		<b>.</b> .		-

## $Q_{rr}$

- **Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 22.5 mH,  $I_{AS}$  = 3.2 A,  $V_{DD}$  = 50 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C. 3.  $I_{SD}$  ≤ 3.2 A, di/dt ≤ 200 A/ $\mu$ s,  $V_{DD}$  ≤ BV $_{DSS}$ , starting  $T_{J}$  = 25°C. 4. Essentially independent of operating temperature.

Reverse Recovery Charge

μС

0.4

 $dI_F / dt = 100 A/\mu s$ 

## **Typical Characteristics**

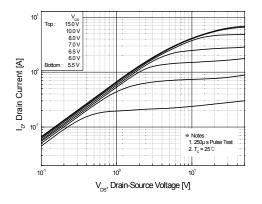


Figure 1. On-Region Characteristics

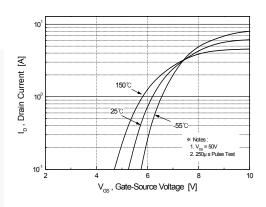


Figure 2. Transfer Characteristics

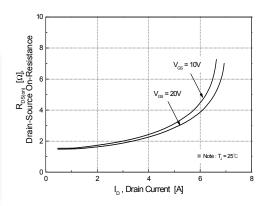


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

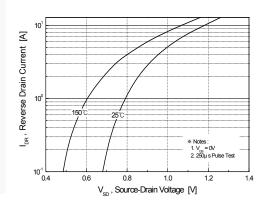


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

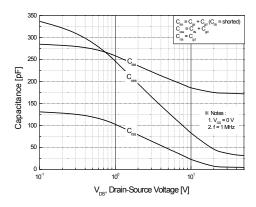


Figure 5. Capacitance Characteristics

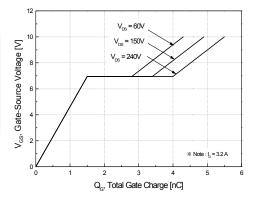


Figure 6. Gate Charge Characteristics

## Typical Characteristics (continued)

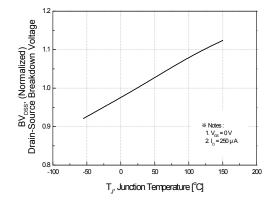
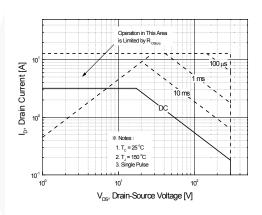


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



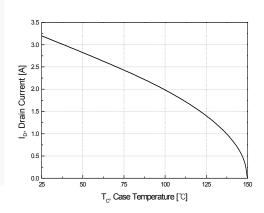


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

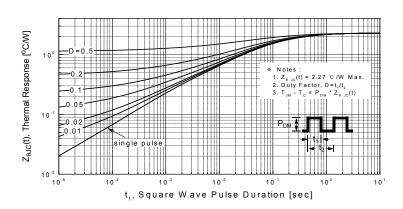


Figure 11. Transient Thermal Response Curve

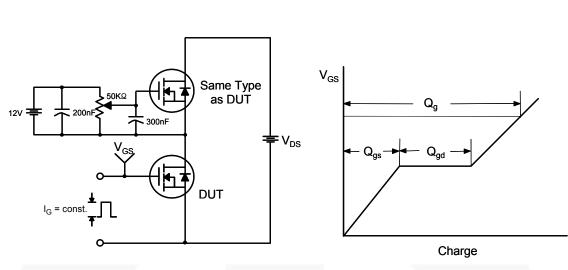


Figure 12. Gate Charge Test Circuit & Waveform

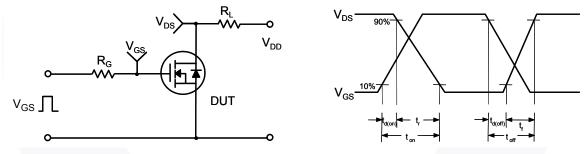


Figure 13. Resistive Switching Test Circuit & Waveforms

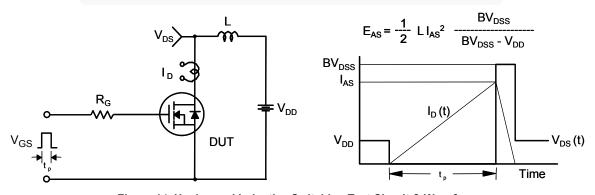
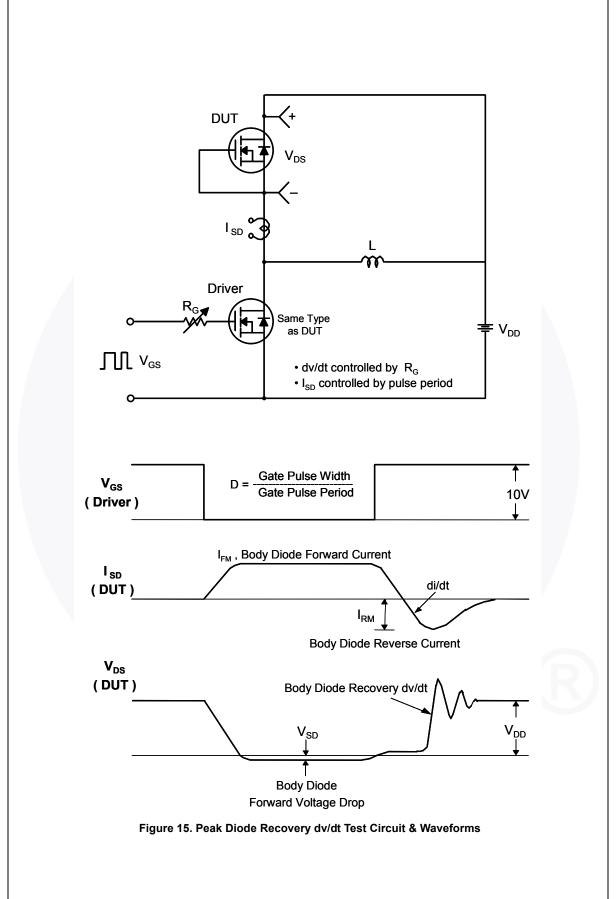
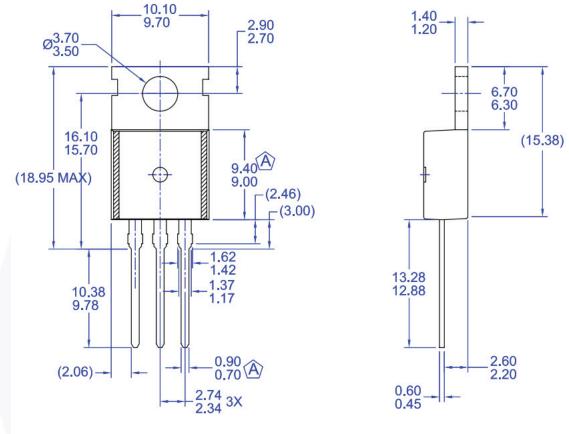


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**



4.70 4.30

9.80

#### NOTES:

- (A) CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

#### Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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